

Small Signal MOSFET

115 mAmps, 60 Volts

N-Channel SOT-88

- Pb-Free Package is Available.

MAXIMUM RATINGS

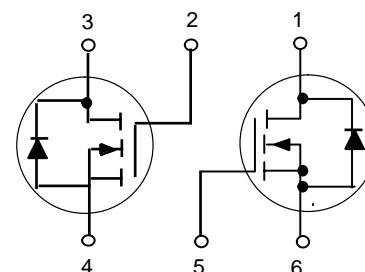
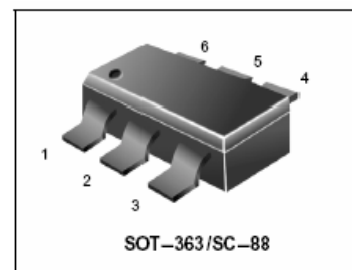
Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	60	Vdc
Drain-Gate Voltage ($R_{GS} = 1.0\text{ M}\Omega$)	V_{DGR}	60	Vdc
Drain Current - Continuous $T_C = 25^\circ\text{C}$ (Note 1) $T_C = 100^\circ\text{C}$ (Note 1) - Pulsed (Note 2)	I_D I_B I_{DM}	± 115 ± 75 ± 800	mAdc
Gate-Source Voltage - Continuous - Non-repetitive ($t_p \leq 50\ \mu\text{s}$)	V_{GS} V_{GSM}	± 20 ± 40	Vdc Vpk

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation Per Device FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	380 250	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	328	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in

L2N7002DW1T1G/T3G



ORDERING INFORMATION

Device	Marking	Shipping
L2N7002DW1T1G	K2	3000 Tape & Reel
L2N7002DW1T3G	K2	10000 Tape & Reel

L2N7002DW1T1G/T3G
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain–Source Breakdown Voltage ($V_{GS} = 0, I_D = 10 \mu\text{Adc}$)	$V_{(BR)DSS}$	60	–	–	Vdc
Zero Gate Voltage Drain Current ($V_{GS} = 0, V_{DS} = 60 \text{ Vdc}$)	I_{DSS}	– –	– –	1.0 500	μAdc
Gate–Body Leakage Current, Forward ($V_{GS} = 20 \text{ Vdc}$)	I_{GSSF}	–	–	100	nAdc
Gate–Body Leakage Current, Reverse ($V_{GS} = -20 \text{ Vdc}$)	I_{GSSR}	–	–	-100	nAdc

ON CHARACTERISTICS (Note 2.)

Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 250 \mu\text{Adc}$)	$V_{GS(th)}$	1.0	–	2.5	Vdc
On–State Drain Current ($V_{DS} \geq 2.0 V_{DS(on)}, V_{GS} = 10 \text{ Vdc}$)	$I_{D(on)}$	500	–	–	mA
Static Drain–Source On–State Voltage ($V_{GS} = 10 \text{ Vdc}, I_D = 500 \text{ mAdc}$) ($V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mAdc}$)	$V_{DS(on)}$	– –	– –	3.75 0.375	Vdc
Static Drain–Source On–State Resistance ($V_{GS} = 10 \text{ V}, I_D = 500 \text{ mAdc}$) $T_C = 25^\circ\text{C}$ $T_C = 125^\circ\text{C}$ ($V_{GS} = 5.0 \text{ Vdc}, I_D = 50 \text{ mAdc}$) $T_C = 25^\circ\text{C}$ $T_C = 125^\circ\text{C}$	$r_{DS(on)}$	– – – –	– – – –	7.5 13.5 7.5 13.5	Ohms
Forward Transconductance ($V_{DS} \geq 2.0 V_{DS(on)}, I_D = 200 \text{ mAdc}$)	g_{FS}	80	–	–	mmhos

DYNAMIC CHARACTERISTICS

Input Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{iss}	–	–	50	pF
Output Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{oss}	–	–	25	pF
Reverse Transfer Capacitance ($V_{DS} = 25 \text{ Vdc}, V_{GS} = 0, f = 1.0 \text{ MHz}$)	C_{rss}	–	–	5.0	pF

SWITCHING CHARACTERISTICS (Note 2.)

Turn–On Delay Time	($V_{DD} = 25 \text{ Vdc}, I_D \cong 500 \text{ mAdc},$ $R_G = 25 \Omega, R_L = 50 \Omega, V_{gen} = 10 \text{ V}$)	$t_{d(on)}$	–	–	20	ns
Turn–Off Delay Time		$t_{d(off)}$	–	–	40	ns

BODY–DRAIN DIODE RATINGS

Diode Forward On–Voltage ($I_S = 11.5 \text{ mAdc}, V_{GS} = 0 \text{ V}$)	V_{SD}	–	–	-1.5	Vdc
Source Current Continuous (Body Diode)	I_S	–	–	-115	mAdc
Source Current Pulsed	I_{SM}	–	–	-800	mAdc

 2. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

L2N7002DW1T1G/T3G

TYPICAL ELECTRICAL CHARACTERISTICS

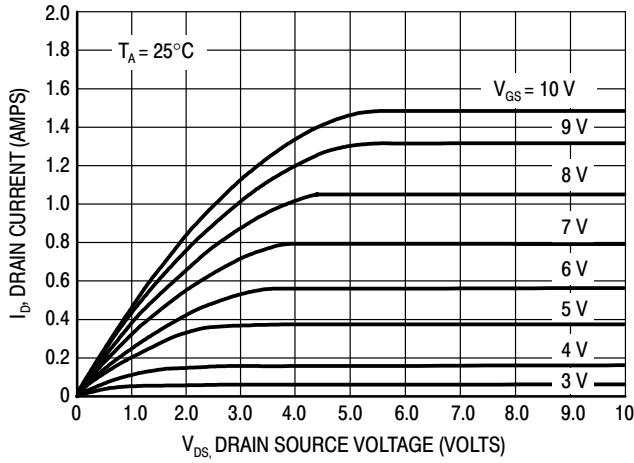


Figure 1. Ohmic Region

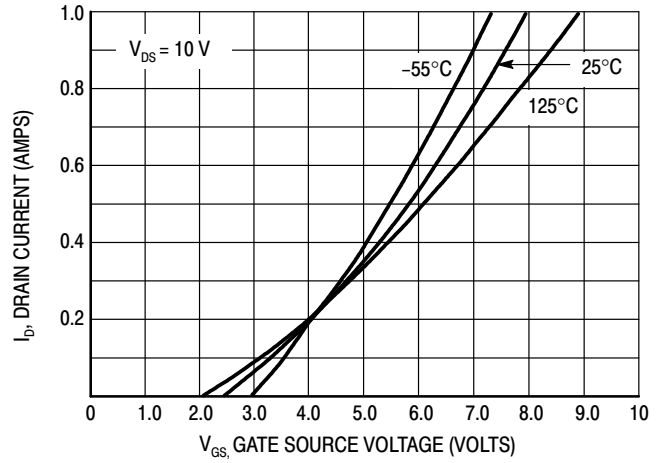


Figure 2. Transfer Characteristics

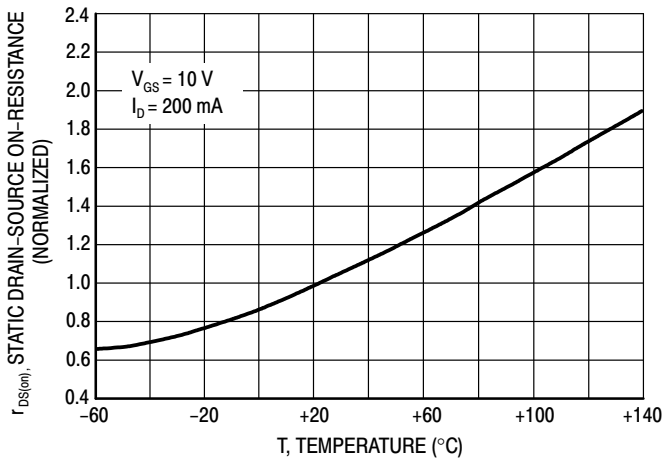


Figure 3. Temperature versus Static Drain-Source On-Resistance

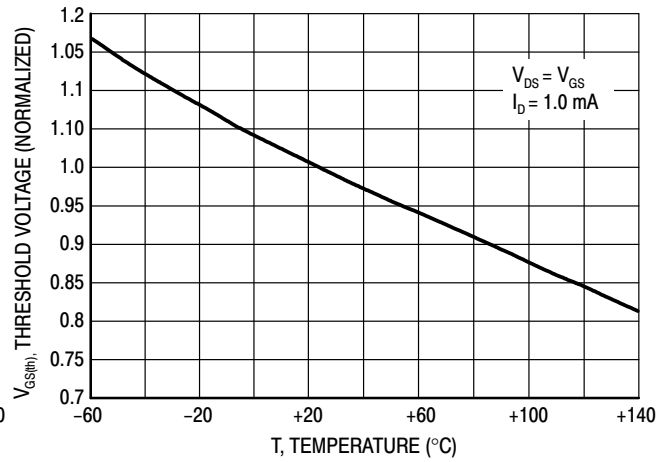
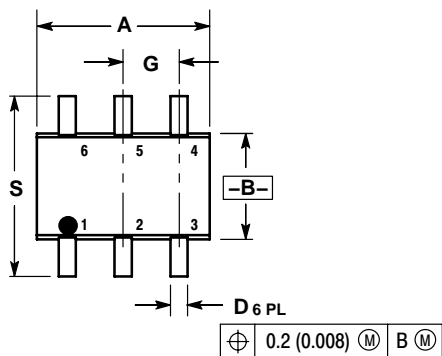


Figure 4. Temperature versus Gate Threshold Voltage

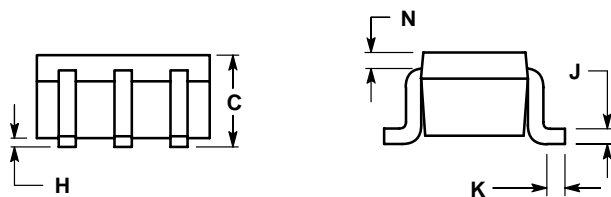
L2N7002DW1T1G/T3G

SC-88 (SOT-363)
CASE 419B-02
ISSUE T



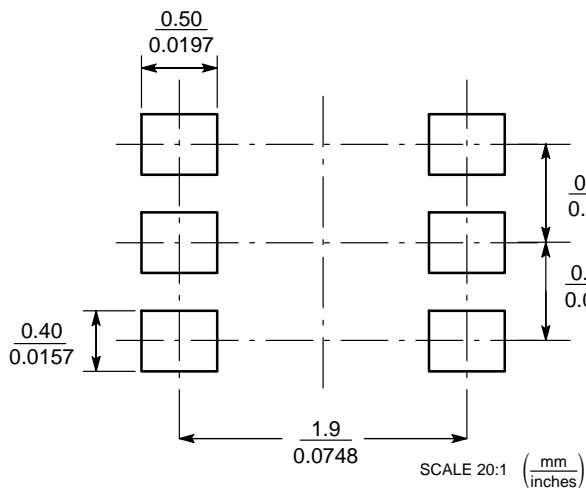
- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. 419B-01 OBSOLETE, NEW STANDARD 419B-02.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.071	0.087	1.80	2.20
B	0.045	0.053	1.15	1.35
C	0.031	0.043	0.80	1.10
D	0.004	0.012	0.10	0.30
G	0.026	BSC	0.65	BSC
H	---	0.004	---	0.10
J	0.004	0.010	0.10	0.25
K	0.004	0.012	0.10	0.30
N	0.008	REF	0.20	REF
S	0.079	0.087	2.00	2.20

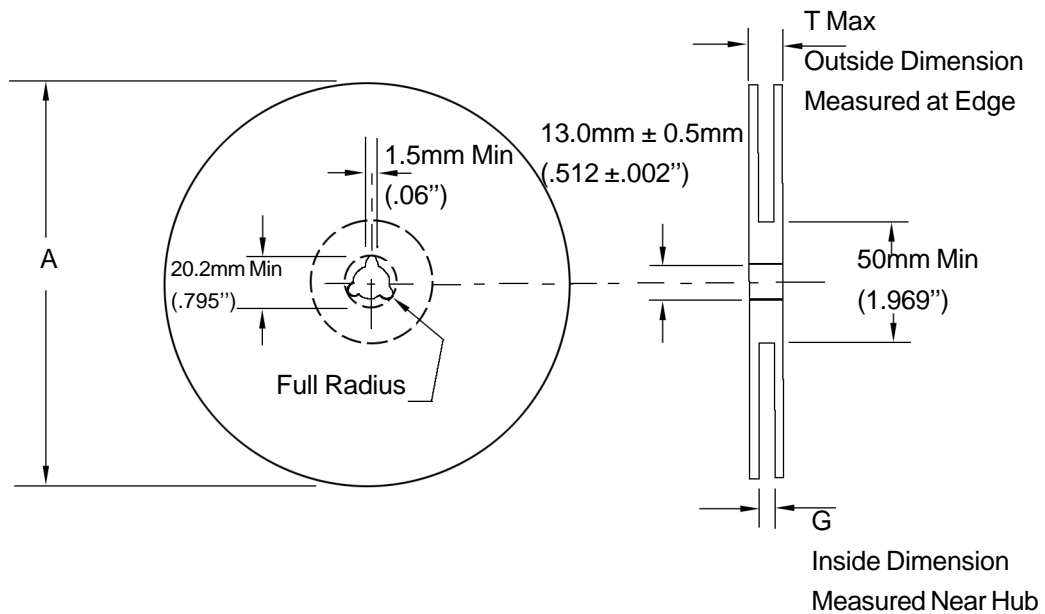


- STYLE 1:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2

SOLDERING FOOTPRINT*



EMBOSSED TAPE AND REEL DATA FOR DISCRETES



Size	A Max	G	T Max
8 mm	330mm (12.992")	8.4mm+1.5mm, -0.0 (.33"+.059", -0.00)	14.4mm (.56")
12mm	330mm (12.992")	12.4mm+2.0mm, -0.0 (.49 "+ .079", -0.00)	18.4mm (.72")
16mm	360mm (14.173")	16.4mm+2.0mm, -0.0 (.646"+.078", -0.00)	22.4mm (.882")
24 mm	360mm (14.173")	24.4mm+2.0mm, -0.0 (.961"+.070", -0.00)	30.4mm (1.197")

Reel Dimensions

Metric Dimensions Govern — English are in parentheses for reference only

Storage Conditions

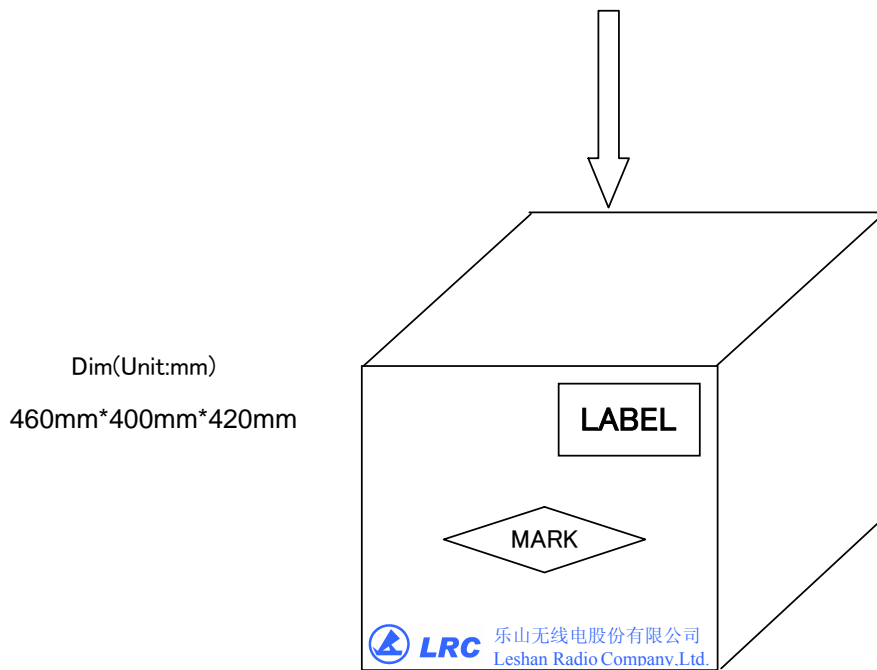
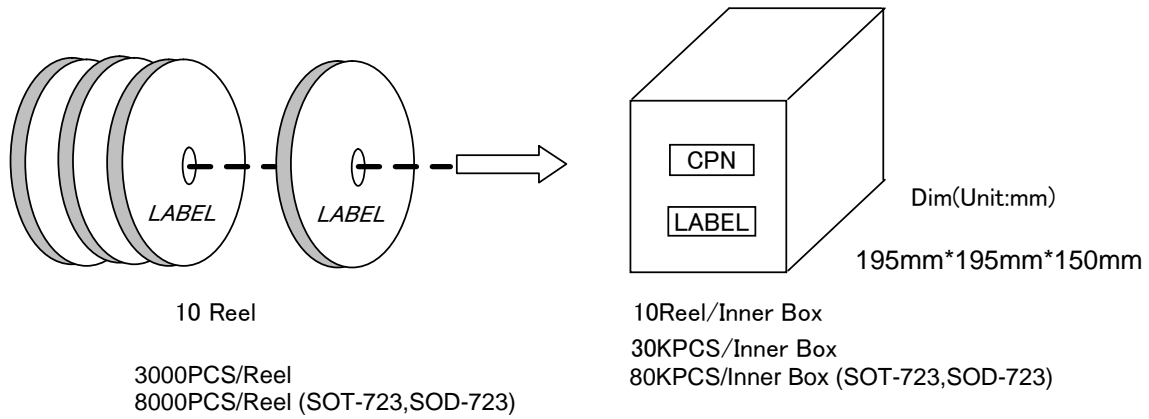
Temperature: 5 to 40 Deg.C (20 to 30 Deg. C is preferred)

Humidity: 30 to 80 RH (40 to 60 is preferred)

Recommended Period: One year after manufacturing

(This recommended period is for the soldering condition only. The characteristics and reliabilities of the products are not restricted to this limitation)

Shipment Specification



12 Inner Box/Carton

360KPCS/Carton
960KPCS/Carton (SOT-723,SOD-723)